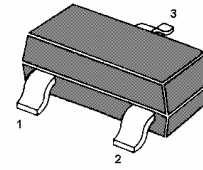


BCW68

PNP Silicon Epitaxial Planar Transistor

for high current application

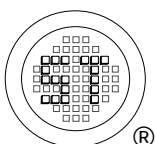
The transistor is subdivided into three groups F, G and H according to its DC current gain.



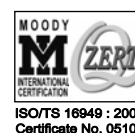
1.BASE 2.EMITTER 3.COLLECTOR
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	60	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	45	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current	$-I_{\text{C}}$	800	mA
Peak Collector Current	$-I_{\text{CM}}$	1	A
Base Current	$-I_{\text{B}}$	100	mA
Peak Base Current	$-I_{\text{BM}}$	200	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{s}	- 55 to + 150	$^\circ\text{C}$



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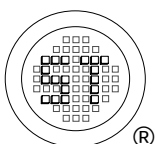


Dated : 06/03/2007

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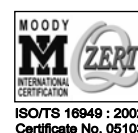
Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE} = 10\text{ V}$, $-I_C = 100\text{ }\mu\text{A}$	F h_{FE}	35	-	-	-
	G h_{FE}	50	-	-	-
	H h_{FE}	80	-	-	-
at $-V_{CE} = 1\text{ V}$, $-I_C = 10\text{ mA}$	F h_{FE}	75	-	-	-
	G h_{FE}	120	-	-	-
	H h_{FE}	180	-	-	-
at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$	F h_{FE}	100	-	250	-
	G h_{FE}	160	-	400	-
	H h_{FE}	250	-	630	-
at $-V_{CE} = 2\text{ V}$, $-I_C = 500\text{ mA}$	F h_{FE}	35	-	-	-
	G h_{FE}	60	-	-	-
	H h_{FE}	100	-	-	-
Collector Cutoff Current at $-V_{CB} = 45\text{ V}$	$-I_{CBO}$	-	-	20	nA
Emitter Cutoff Current at $-V_{EB} = 4\text{ V}$	$-I_{EBO}$	-	-	20	nA
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	45	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{CE(sat)}$	-	-	0.3	V
Collector Emitter Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$	$-V_{CE(sat)}$	-	-	0.7	V
Base Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{BE(sat)}$	-	-	1.25	V
Base Emitter Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$	$-V_{BE(sat)}$	-	-	2	V
Transition Frequency at $-V_{CE} = 5\text{ V}$, $-I_C = 50\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	200	-	MHz
Collector Base Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	6	-	pF
Emitter Base Capacitance at $-V_{BE} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	60	-	pF



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